

Description

The BSC042N03LSG uses advanced trench technology

to provide excellent $R_{DS(ON)}$, low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



 $V_{DS} = 30V I_{D} = 120A$

 $R_{DS(ON)} < 4.4 \text{mÙ V}_{GS} = 10 \text{V}$

Application

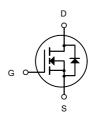
Battery protection

Load switch

Uninterruptible power supply



DFN5X6-8L



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
BSC042N03LSG	DFN5X6-8L	042N03LS XXXX	5000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

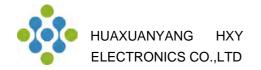
Symbol	Parameter	Rating	Units	
Vps	Drain-Source Voltage	30	V	
Vgs	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ^{1,6}	120	А	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ^{1,6}	66	А	
Ідм	Pulsed Drain Current ²	320	А	
EAS	Single Pulse Avalanche Energy³	180	mJ	
las	Avalanche Current	60	А	
P _D @T _C =25°C	Total Power Dissipation ⁴	187	W	
Тѕтс	Storage Temperature Range -55 to		°C	
TJ	T _J Operating Junction Temperature Range		°C	
R _θ JA	Thermal Resistance Junction-Ambient ¹ 62		°C/W	
Rejc	Reuc Thermal Resistance Junction-Case ¹		°C/W	



N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	DI Parameter Conditions		Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
2BVoss/2TJ	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =1mA		0.014		V/°C
		V _{GS} =10V , I _D =30A		3.5	4.4	
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =15A		4.6	5.8	$\mathbf{m}\Omega$
V _{GS(th)}	Gate Threshold Voltage		1.2		2.5	V
$\mathbb{P}V_{\text{GS(th)}}$	V _{GS(th)} Temperature Coefficient	 V _{GS} =V _{DS} , I _D =250uA		-4		mV/°C
Ipss	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =25°C			1	
		V _{DS} =24V , V _{GS} =0V , T _J =55°C			5	uA
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =30A		50		S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.7		Ω
Qg	Total Gate Charge (4.5V)			56.9		
Qgs	Gate-Source Charge	V _{DS} =15V , V _{GS} =10V , I _D =15A		13.8		nC
Qgd	Gate-Drain Charge			23.5		
Td(on)	Turn-On Delay Time			20.1		
Tr	Rise Time	V _{DD} =15V , V _{GS} =10V ,		6.3		
Td(off)	Turn-Off Delay Time	—R _G =3.3 , I _D =1A		124.6		ns
T _f	Fall Time			15.8		
Ciss	Input Capacitance			4345		
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		340		pF
Crss	Reverse Transfer Capacitance	1		225		
Is	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			85	Α
VsD	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1.2	V
			1			



Typical Characteristics

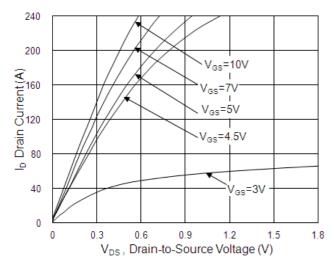


Fig.1 Typical Output Characteristics

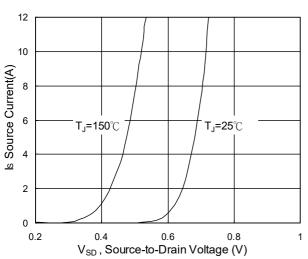


Fig.3 Forward Characteristics of Reverse

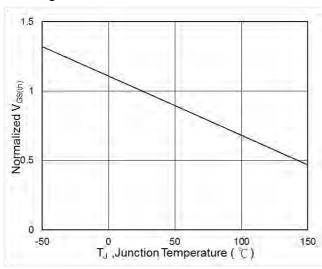


Fig.5 Normalized $V_{\text{GS(th)}}$ v.s T_{J}

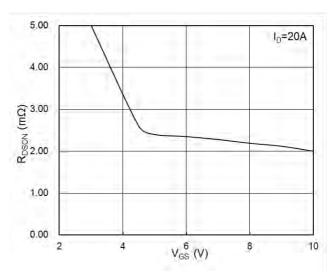


Fig.2 On-Resistance v.s Gate-Source

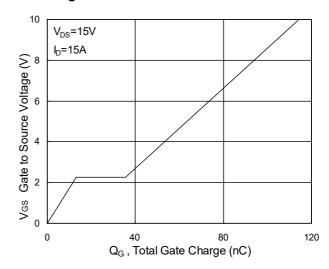


Fig.4 Gate-Charge Characteristics

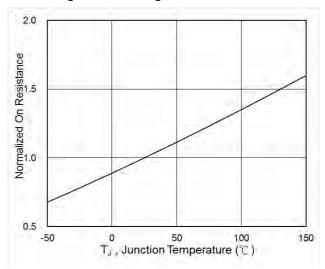


Fig.6 Normalized R_{DSON} v.s T_J

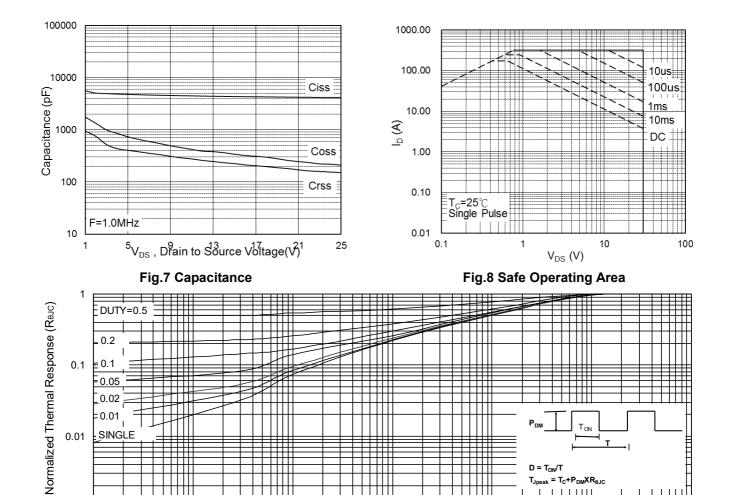
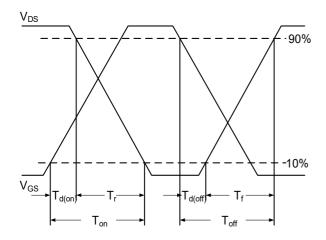


Fig.9 Normalized Maximum Transient Thermal Impedance

t, Pulse Width (s)

0.001



0.0001

0.0001

Fig.10 Switching Time Waveform

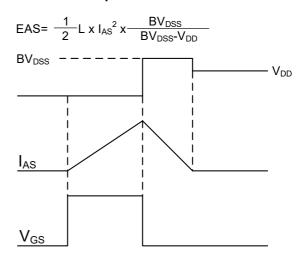
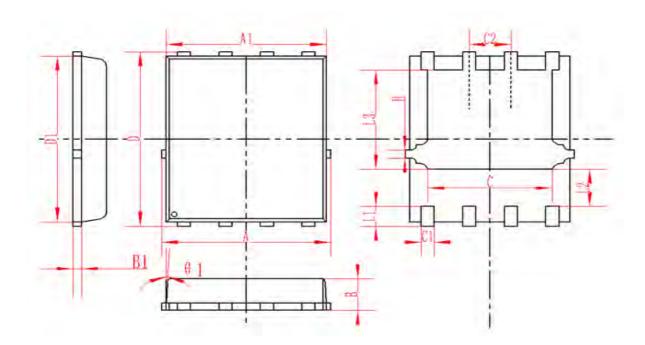


Fig.11 Unclamped Inductive Switching Waveform



DFN5X6-8L Package Information



SYMBOL	MM		INCH				
	MIN	NOM	MAX	MIN	NOM	MAX	
А	4.95	5	5.05	0.195	0.197	0.199	
A1	4.82	4.9	4.98	0.190	0.193	0.196	
D	5.98	6	6.02	0.235	0.236	0.237	
D1	5.67	5.75	5.83	0.223	0.226	0.230	
В	0.9	0.95	1	0.035	0.037	0.039	
B1	0.254REF		0.010REF				
С	3.95	4	4.05	0.156	0.157	0.159	
C1	0.35	0.4	0.45	0.014	0.016	0.018	
C2	1.27TYP		0.5TYP				
θ1	8°	10°	12°	8°	10°	12°	
L1	0.63	0.64	0.65	0.025	0.025	0.026	
L2	1.2	1.3	1.4	0.047	0.051	0.055	
L3	3.415	3.42	3.425	0.134	0.135	0.135	
Н	0.24	0.25	0.26	0.009	0.010	0.010	



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